



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Diodes

BAS40 SERIES

SCHOTTKY DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}\text{C}$)

Forward Current

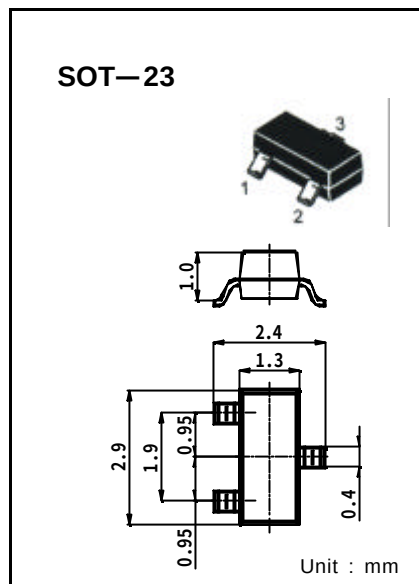
I_F : 200 mA

Reverse Voltage

V_R : 40 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150$



BAS40 Marking:43

BAS40-04

Marking:44

BAS40-05

Marking:45

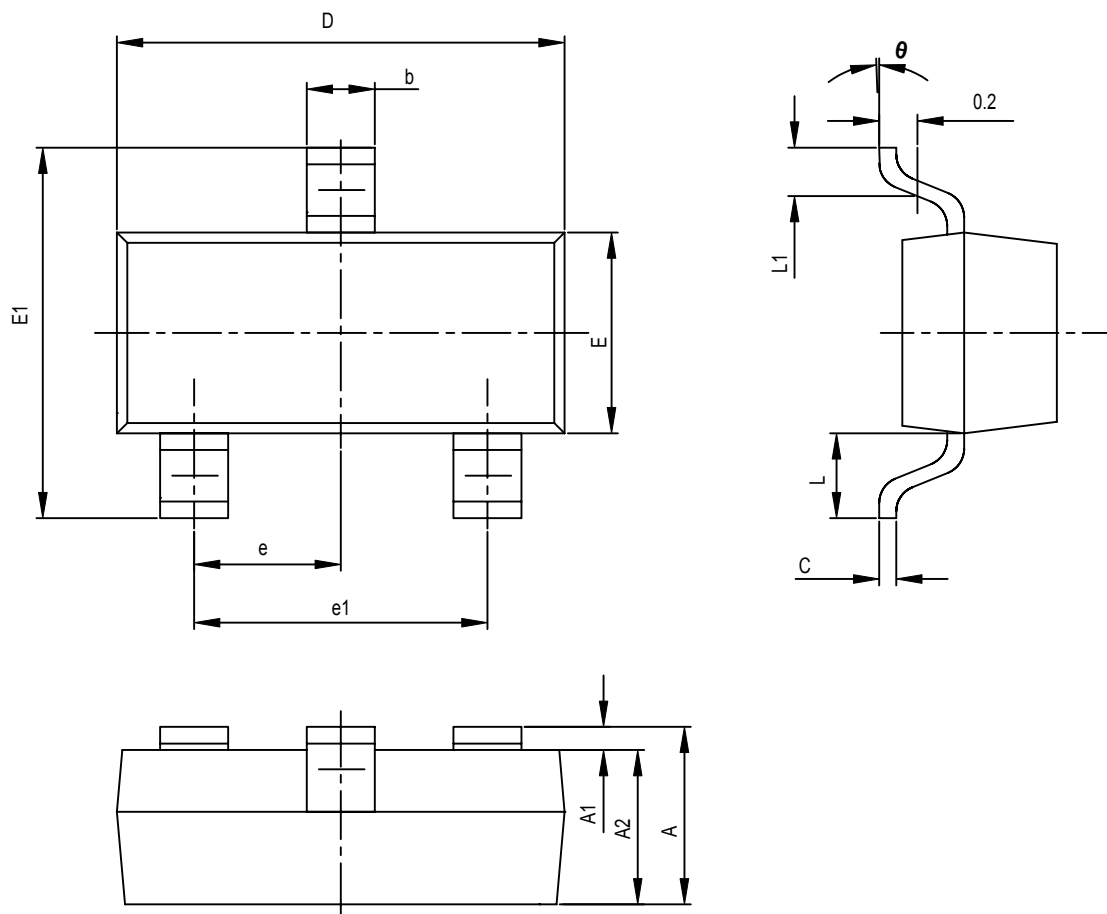
BAS40-06

Marking:46

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	40		V
Reverse voltage leakage current	I_R	$V_R=30\text{V}$		100	nA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=40\text{mA}$		380 1000	mV
Diode capacitance	C_D	$V_R=0\text{V}$ $f=1\text{MHz}$		5	pF
Reverse recovery time	t_{rr}	$I_F=10\text{mA}$ through $I_R=10\text{mA}$ to $I_R=1\text{mA}$		5	nS

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TPY		0.037TPY	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°